

# **MOSFET** - Power, Single P-Channel, SOT-23

-60 V, 230 mΩ, -1.1 A

### NVR5124PL

#### **Features**

- Trench Technology
- NVR Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

#### **MAXIMUM RATINGS** ( $T_J = 25^{\circ}C$ unless otherwise noted)

Parar	Symbol	Value	Unit		
Drain-to-Source Voltag	V <sub>DSS</sub>	-60	٧		
Gate-to-Source Voltage	9		V <sub>GS</sub>	±20	V
Continuous Drain	Steady	, ,		-1.1	Α
Current R <sub>θJA</sub> (Notes 1, 2, 3)	State T <sub>A</sub> = 100°C			-0.67	
Power Dissipation		T <sub>A</sub> = 25°C	$P_{D}$	0.47	W
R <sub>θJA</sub> (Notes 1, 2)		T <sub>A</sub> = 100°C		0.19	
Pulsed Drain Current	$T_A = 25$	°C, t <sub>p</sub> = 10 μs	I <sub>DM</sub>	25	Α
Operating Junction and Storage Temperature Range			T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
Source Current (Body Diode)			I <sub>S</sub>	-0.6	Α
Lead Temperature for S (1/8" from case for 10 s)		urposes	T <sub>L</sub>	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

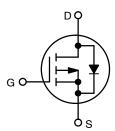
#### THERMAL RESISTANCE MAXIMUM RATINGS (Note 1)

Parameter	Symbol	Value	Unit
Junction-to-Ambient - Steady State (Note 2)	$R_{\theta JA}$	268	°C/W

- The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
- 2. Surface-mounted on FR4 board using a 650 mm<sup>2</sup>, 2 oz. Cu pad.
- 3. Continuous DC current rating. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> MAX	I <sub>D</sub> MAX	
-60 V	230 m $\Omega$ @ –10 V	-1.1 A	
	365 m $\Omega$ @ –4.5 V	-1.1 <i>X</i>	

#### P-Channel





#### SOT-23 CASE 318 STYLE 21

#### MARKING DIAGRAM/ PIN ASSIGNMENT



V24 = Device Code M = Date Code\* ■ = Pb-Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NVR5124PLT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, <a href="https://example.com/BRD8011/D">BRD8011/D</a>.

<sup>\*</sup>Date Code orientation may vary depending upon manufacturing location.

### **ELECTRICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$ unless otherwise noted)

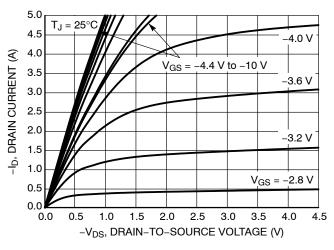
Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS				•	•		
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V}, I_D =$	-250 μA	-60	_	_	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 \text{ V}, \qquad T_{J} = 25^{\circ}\text{C}$		-	-	-1.0	μΑ
		$V_{DS} = -60 \text{ V}$	T <sub>J</sub> = 125°C	-	-	-10	1
Gate-to-Source Leakage Current	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS}$	= ±20 V	-	-	±100	nA
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{GS} = V_{DS}, I_D =$	= -250 μA	-1.5	-	-2.5	V
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	$V_{GS} = -10 \text{ V}, 1$	<sub>D</sub> = -3 A	-	183	230	mΩ
		$V_{GS} = -4.5 V$ ,	I <sub>D</sub> = -3 A	-	280	365	1
Forward Transconductance	9FS	V <sub>DS</sub> = −15 V, I	<sub>D</sub> = -5 A	4	-	-	S
CHARGES AND CAPACITANCES				•	•	•	
Input Capacitance	C <sub>iss</sub>	$V_{GS} = 0 \text{ V, f} = 1.0 \text{ MHz,}$ $V_{DS} = -25 \text{ V}$		_	240	_	pF
Output Capacitance	C <sub>oss</sub>			_	27.6	-	1
Reverse Transfer Capacitance	C <sub>rss</sub>			_	18.5	-	1
Total Gate Charge	Q <sub>G(TOT)</sub>	$V_{GS} = -4.5 \text{ V}, V_{DS} = -48 \text{ V},$ $I_{D} = -3 \text{ A}$		_	2.3	-	nC
Threshold Gate Charge	Q <sub>G(TH)</sub>			_	0.5	-	1
Gate-to-Source Charge	Q <sub>GS</sub>			_	0.9	-	1
Gate-to-Drain Charge	$Q_{GD}$			_	1.0	-	1
Total Gate Charge	Q <sub>G(TOT)</sub>	$V_{GS} = -10 \text{ V}, V_{DS} = -48 \text{ V},$ $I_{D} = -3 \text{ A}$		-	4.3	-	1
SWITCHING CHARACTERISTICS (No	ote 5)			ı	<u>.</u>		
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{GS} = -4.5 \text{ V, } V_{E}$ $I_{D} = -3 \text{ A, } R_{G}$	<sub>OS</sub> = -48 V,	-	6.6	_	ns
Rise Time	t <sub>r</sub>	$I_D = -3 A, R_G$	= 2.5 Ω	_	10.6	_	
Turn-Off Delay Time	t <sub>d(off)</sub>			_	12.2	_	
Fall Time	t <sub>f</sub>			-	3.5	-	1
DRAIN-SOURCE DIODE CHARACTE	RISTICS				•		
Forward Diode Voltage	$V_{SD}$	$V_{GS} = 0 \text{ V},$ $T_{J} = 25^{\circ}\text{C}$ $T_{J} = 125^{\circ}\text{C}$		-	-0.88	-1.0	V
				-	-0.76	-	1
Reverse Recovery Time	t <sub>RR</sub>	V <sub>GS</sub> = 0		-	15	-	ns
Charge Time	ta	$dI_{S}/dt = 100$ $I_{S} = -3$	) A/μs, A	_	13	-	1
Discharge Time	t <sub>b</sub>	- 15 - 371		_	2.4	-	1
Reverse Recovery Charge	Q <sub>RR</sub>	1		_	10	_	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: Pulse Width  $\leq 300~\mu s$ , Duty Cycle  $\leq 2\%$ .

5. Switching characteristics are independent of operating junction temperatures.

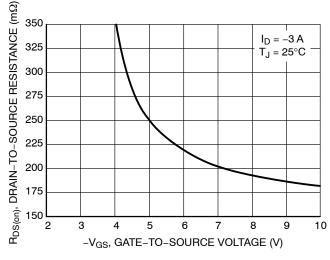
#### **TYPICAL CHARACTERISTICS**



5.0  $V_{DS} = -10 \text{ V}$ 4.5 -ID, DRAIN CURRENT (A) 4.0 3.5 3.0 2.5 2.0  $T_J = 25^{\circ}C$ 1.5 1.0 0.5  $T_J = 125^{\circ}C$  $T_J = -55^{\circ}C$ 0.0 0.0 0.5 1.5 2.0 2.5 3.0 3.5 -V<sub>GS</sub>, GATE-TO-SOURCE VOLTAGE (V)

Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



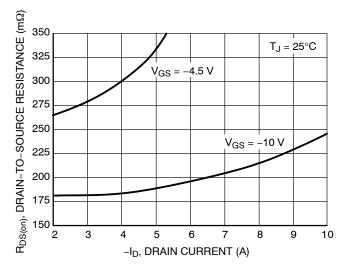
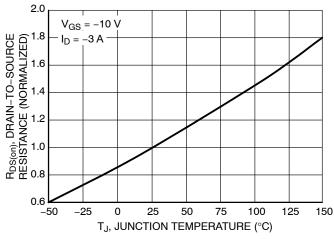


Figure 3. On-Resistance vs. Gate-to-Source Voltage

Figure 4. On–Resistance vs. Drain Current and Gate Voltage



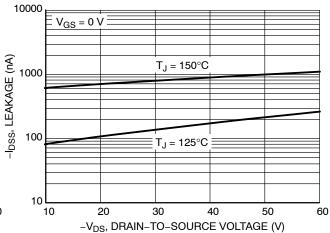
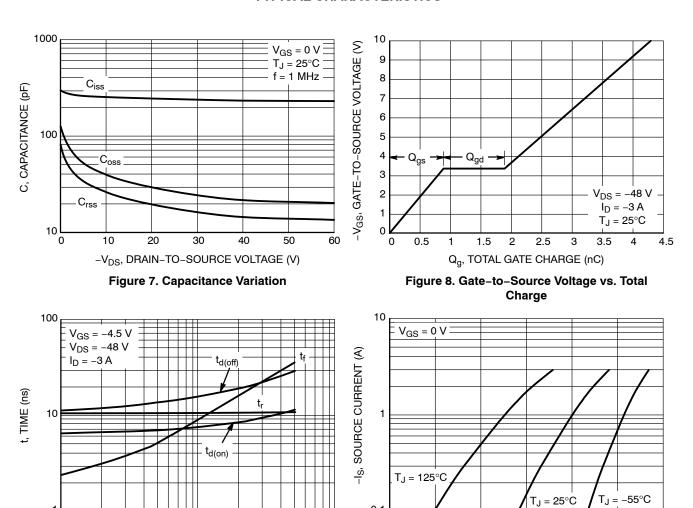


Figure 5. On–Resistance Variation with Temperature

Figure 6. Drain-to-Source Leakage Current vs. Voltage

#### **TYPICAL CHARACTERISTICS**



0.1

0.4

0.5

0.6

Figure 9. Resistive Switching Time Variation vs. Gate Resistance

10

 $R_G$ , GATE RESISTANCE ( $\Omega$ )

Figure 11. Diode Forward Voltage vs. Current

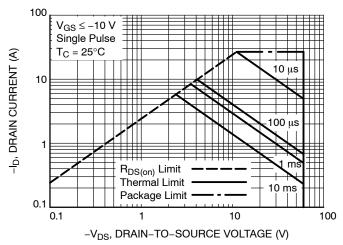
0.7

-V<sub>SD</sub>, SOURCE-TO-DRAIN VOLTAGE (V)

0.8

0.9

1.0



100

Figure 10. Maximum Rated Forward Biased Safe Operating Area

#### **TYPICAL CHARACTERISTICS**

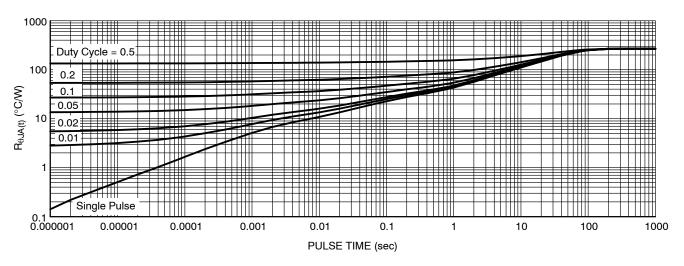


Figure 12. Thermal Response

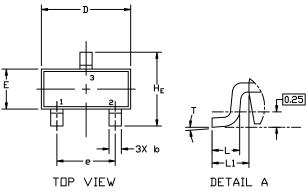




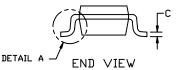
**SOT-23 (TO-236)** CASE 318 ISSUE AT

**DATE 01 MAR 2023** 









#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIM	ETERS			INCHES	
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10°

# GENERIC MARKING DIAGRAM\*

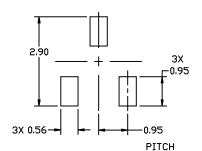


XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

#### **STYLES ON PAGE 2**

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## MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



#### **SOT-23 (TO-236)** CASE 318 ISSUE AT

**DATE 01 MAR 2023** 

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	1	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: I PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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